

IN THE CLAIMS:

Claims 1-32 (cancelled)

Claim 33 (original) A bipolar transistor, comprising:
a collector region;
a base region formed in a base layer overlying the collector region;
an emitter-base dielectric stack overlying the base layer and having an opening therein exposing a portion of the base layer, the emitter-base dielectric stack comprising a carbide layer;
and
an emitter poly layer overlying the emitter-base dielectric stack and an exposed portion of the base layer.

Claim 34 (original) The transistor of claim 33, wherein the emitter-base dielectric stack comprises:

a first oxide layer overlying the base region of the base layer;
a carbide layer overlying the first oxide layer; and
a second oxide layer overlying the carbide layer.

Claim 35 (original) The transistor of claim 34, wherein the first oxide layer comprises:
a thermal silicon oxide layer overlying the base layer and having a thickness of about 20 Å or more and about 50 Å or less; and
a first silicon oxide overlying the thermal silicon oxide layer and having a thickness of about 50 Å.

Claim 36 (original) The transistor of claim 34, wherein the first oxide layer comprises a first silicon oxide overlying the base layer and having a thickness of about 70 Å or more and about 100 Å or less.

Claim 37 (original) The transistor of claim 34, wherein the carbide layer comprises a silicon carbide layer overlying the first oxide layer.

Claim 38 (original) The transistor of claim 37, wherein the silicon carbide layer comprises a thickness of about 100 Å.

Claim 39 (original) The transistor of claim 37, wherein the second oxide layer comprises a second silicon oxide overlying the carbide layer and having a thickness of about 500 Å or more and about 1000 Å or less.